



## Features

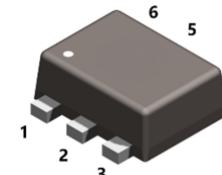
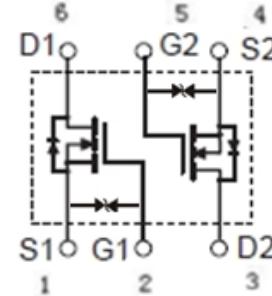
- Low on-resistance
- High-speed switching
- Drive circuits can be simple
- Parallel use is easy
- HBM: JESD22-A114-B: 2

## Typical Applications

- N-channel enhancement mode effect transistor
- Switching application

## Mechanical Data

- Case: SOT-563
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208



**SOT-563**

## Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
2N7002HV	SOT-563	3000 pcs / Tape & Reel	7002K

## Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Gate -Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$I_D$	300	mA
Continuous Drain Current ( $T_A = 70^\circ\text{C}$ ) <sup>*1</sup>		240	mA
Pulsed Drain Current ( $t_p = 10\mu\text{s}$ , $T_A = 25^\circ\text{C}$ )	$I_{DM}$	2000	mA
Single Pulse Avalanche Energy <sup>*3</sup>	$E_{AS}$	0.11	mJ
Power Dissipation ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$P_D$	0.25	W
Operating Junction Temperature Range	$T_J$	-55 ~ +150	°C
Storage Temperature Range	$T_{STG}$	-55 ~ +150	°C

## Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	-	342	°C/W
Thermal Resistance Junction-to-Air <sup>*1</sup>	$R_{\theta JA}$	-	-	500	°C/W



## Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

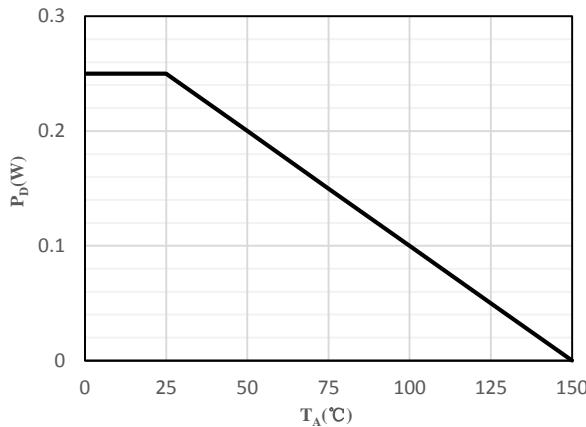
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$ , $I_D = 250\mu\text{A}$	60	-	-	V
$I_{DS}^S$	Drain to Source Leakage Current	$V_{DS} = 60\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate-body Leakage	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b>						
$R_{DS(ON)}$	Drain-Source On-resistance <sup>*2</sup>	$V_{GS} = 10\text{V}$ , $I_D = 0.5\text{A}$	-	1	2.5	$\Omega$
		$V_{GS} = 5\text{V}$ , $I_D = 0.05\text{A}$	-	1.1	3	
		$V_{GS} = 4.5\text{V}$ , $I_D = 0.5\text{A}$	-	1.2	4	
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	1	1.5	2.5	V
<b>Dynamic Characteristics</b>						
$C_{ISS}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 20\text{V}$ $f = 1.0\text{MHz}$	-	26.7	-	pF
$C_{OSS}$	Output Capacitance		-	7.1	-	
$C_{RSS}$	Reverse Transfer Capacitance		-	2.2	-	
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time <sup>*4</sup>	$V_{DD} = 30\text{V}$ , $I_D = 0.2\text{A}$ $V_{GS} = 10\text{V}$ , $R_G = 25\Omega$ $R_L = 150\Omega$	-	6	-	ns
$t_r$	Turn-on Rise Time <sup>*4</sup>		-	5	-	
$t_{d(off)}$	Turn-Off Delay Time <sup>*4</sup>		-	25	-	
$t_f$	Turn-Off Fall Time <sup>*4</sup>		-	15	-	
$Q_G$	Total Gate-Charge	$V_{DS} = 10\text{V}$ $V_{GS} = 4.5\text{V}$ $I_D = 0.2\text{A}$	-	0.44	-	nC
$Q_{GS}$	Gate to Source Charge		-	0.14	-	nC
$Q_{GD}$	Gate to Drain (Miller) Charge		-	0.2	-	nC
<b>Source-Drain Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage <sup>*2</sup>	$I_S = 0.3\text{A}$ , $V_{GS} = 0\text{V}$	-	0.85	1.2	V

Notes:

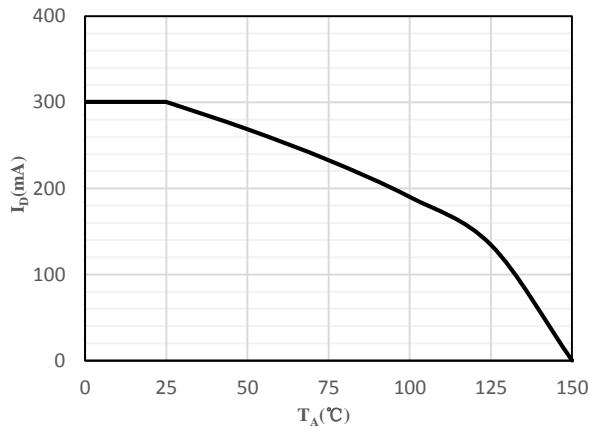
1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
3. The  $E_{AS}$  data shows Max. rating. The test condition is  $V_{DD} = 30\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $L = 0.1\text{mH}$
4. Guaranteed by design, not subject to production



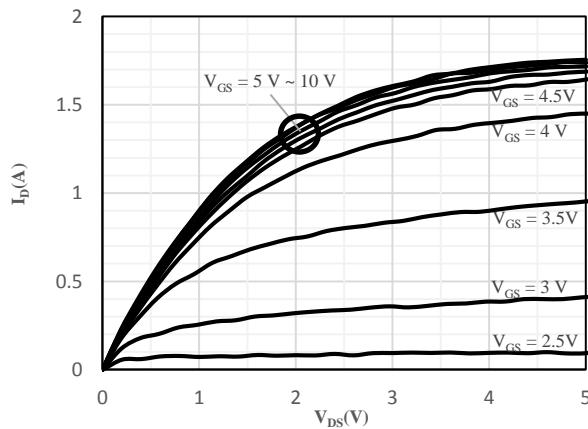
## Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)



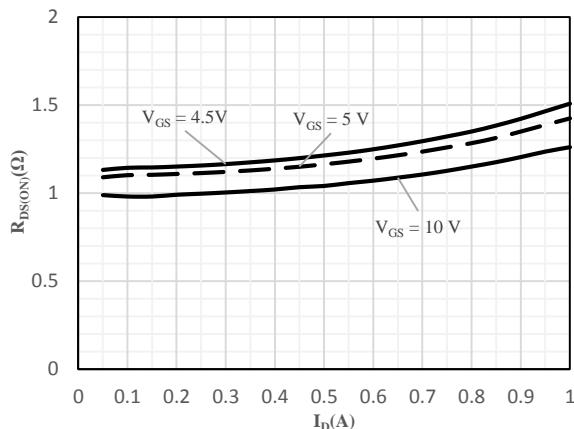
**Fig 1 Power Dissipation**



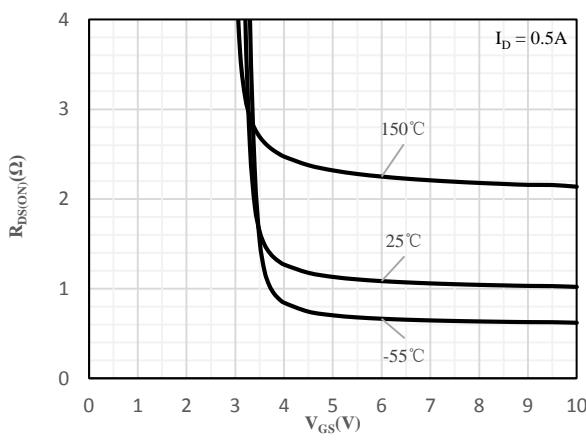
**Fig 2 Drain Current**



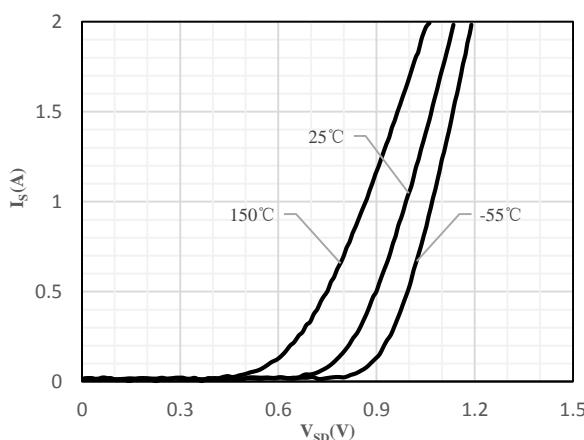
**Fig 3 Typical Output Characteristics**



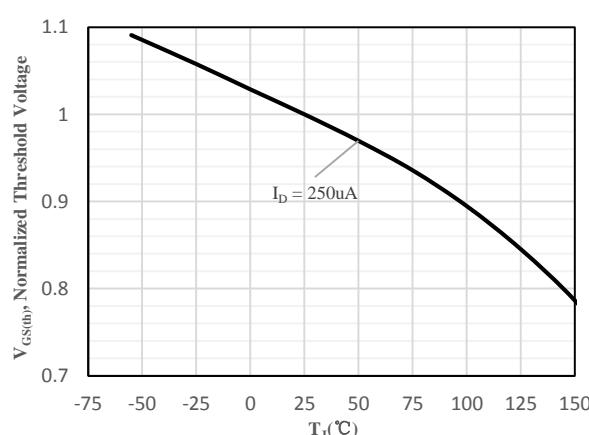
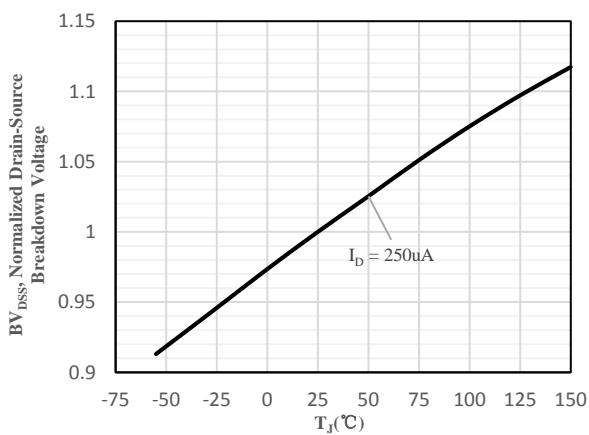
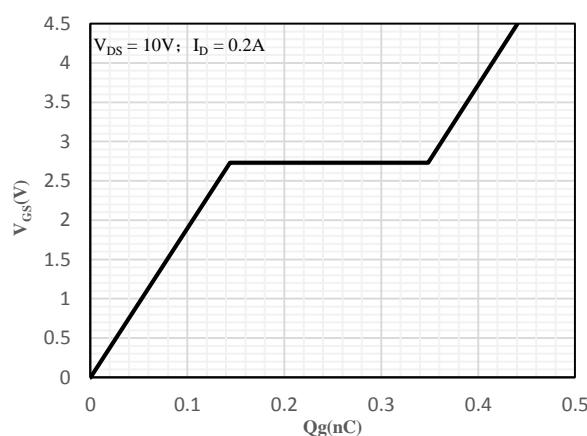
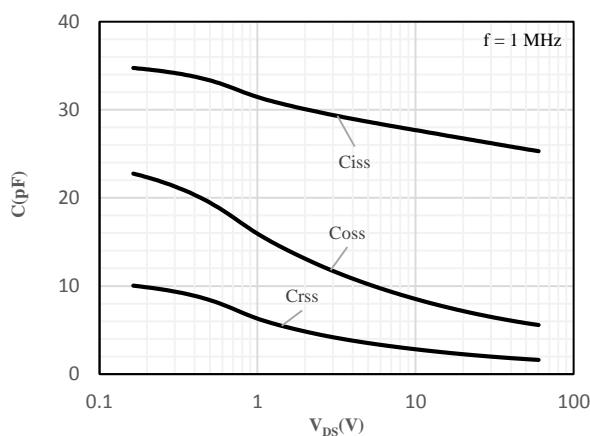
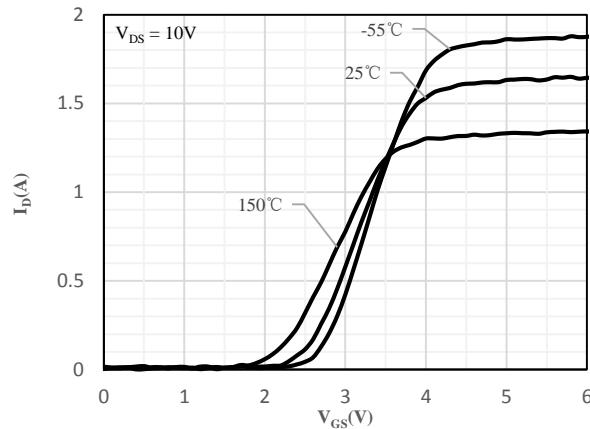
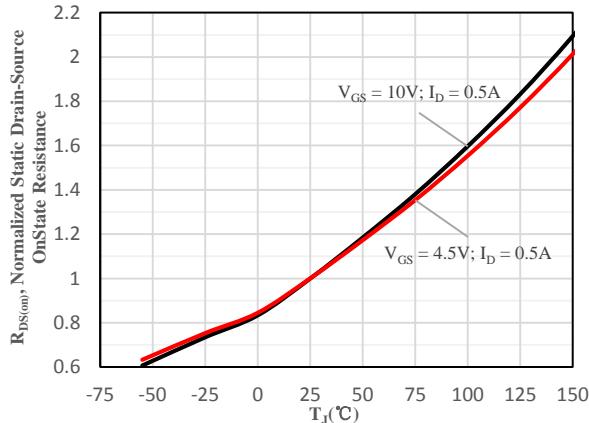
**Fig 4 On-Resistance vs. Drain Current and Gate Voltage**

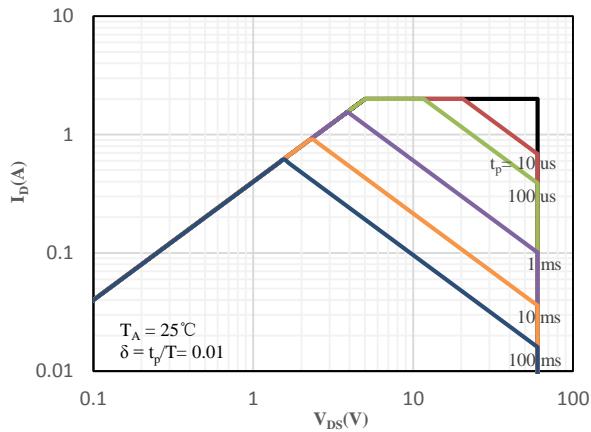
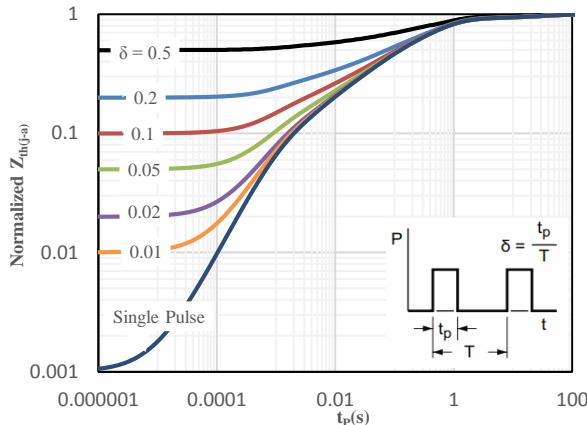


**Fig 5 On-Resistance vs. Gate-Source Voltage**



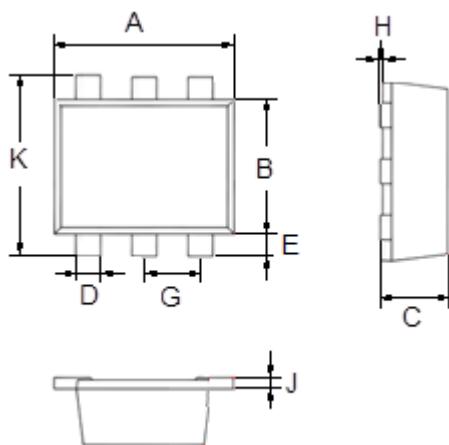
**Fig 6 Body-Diode Characteristics**




**Fig 13 Safe Operating Area**

**Fig 14 Normalized Maximum transient thermal impedance**



### Package Outline Dimensions (Unit: mm)



SOT-563		
Dimension	Min.	Max.
A	1.500	1.700
B	1.100	1.300
C	0.525	0.600
D	0.170	0.270
E	0.100	0.300
G	0.450	0.550
H	0.000	0.050
J	0.090	0.160
K	1.500	1.700

### Mounting Pad Layout (Unit: mm)

**SOT-563**

